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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18
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Title of Invention

HIGH PERFORMANCE CMOS DEVICE STRUCTURES AND METHOD OF MANUFACTURE

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10/604190

Confirmation Number:

1189

First Named Applicant:

Bruce Doris

Attorney Docket Number: FIS920030152US1

Art Unit:

2818

Examiner:

David Vu

Search string:

(6228694 or 6406973 or 6281532 or 5683934 or 6368931 or 5310446 or 4853076 or 6509618 or 6476462 or 6362082 or 6228694 or 5565697 or 6521964 or 6506652 or 5081513 or 3602841 or 6531740 or 6531369 or 6501121 or 6498358 or 6493497 or 6403975 or 6361885 or 6255169 or 6246095 or 6165383 or 6133071 or 6046464 or 6025280 or 5940736 or 5880040 or 5861651 or 5679965 or 5670798 or 5561302 or 5471948 or 5459346 or 5391510 or 5371399 or 5108843 or 5060030 or 4958213 or 4665415 or 5989978 or 6284626 or 6274444 or 6261964 or 6221735 or 6117722 or 6107143 or 6090684 or 6066545 or 6008126 or 5840593 or 5592007 or 5571741 or 5557122 or 5354695 or 5134085 or 5006913 or 4952524 or 4855245 or 6573172 or 6621131 or 20030040158 or 20020090791 or 20020074598 or 20020086472).pn.

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Signature

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Date

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